

DATA SHEET

DESCRIPTION	PHOTO TRIAC
APPLICATION	PHOTO SENSOR
ISSUED DATE	2026-01-02



Opto Device Technology

Photo Triac Specification

No.	Device Name	Chip Specification					Application	Remarks
		Chip Size	Thickness	Passivation (Material)	M1 Pad Size	M2 Pad Size		
		(mm×mm) (mil×mil)	(μm) (mil)		(μm×μm) (mil×mil)	(μm×μm) (mil×mil)		
1	OSTA1104B(200)	1.04*1.04 (40.94*40.94)	300 (11.81)	Silicon Nitride	Φ145 (Φ5.71)	Φ145 (Φ5.71)		Random Phase (Non Zero Crossing)
2	OSTA1104B(320)	1.04*1.04 (40.94*40.94)	290 (11.42)	Silicon Nitride	Φ145 (Φ5.71)	Φ145 (Φ5.71)		Random Phase (Non Zero Crossing)
3	OSTA1104C(200)	1.04*1.04 (40.94*40.94)	300 (11.81)	Silicon Nitride	Φ145 (Φ5.71)	Φ145 (Φ5.71)		Random Phase (Non Zero Crossing)
4	OSTA1104C(320)	1.04*1.04 (40.94*40.94)	290 (11.42)	Silicon Nitride	Φ145 (Φ5.71)	Φ145 (Φ5.71)		Random Phase (Non Zero Crossing)
5	OSTA1104C	1.04*1.04 (40.94*40.94)	220 (8.66)	Silicon Nitride	Φ145 (Φ5.71)	Φ145 (Φ5.71)		Random Phase (Non Zero Crossing)
6	OSTZ3120	1.20*1.20 (47.24*47.24)	290 (11.42)	Silicon Nitride	140*140 (5.51*5.51)	140*140 (5.51*5.51)		Zero Crossing



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